

# Physics of Thin Films

*Advances in Research and Development*

ZANNE L. ROHDE  
CHRISTOPH STEINBRÜCHEL

## PLASMA SOURCES FOR THIN FILM DEPOSITION AND ETCHING

*Edited by*

**Maurice H. Francombe**

*Department of Physics  
The University of Pittsburgh  
Pittsburgh, Pennsylvania*

**John L. Vossen**

*John Vossen Associates  
Technical and Scientific Consulting  
Bridgewater, New Jersey*

531.082  
P567  
Vol. 18  
1994  
SCIENCE

AUG 25 1994



**Academic Press**  
San Diego New York Boston  
London Sydney Tokyo Toronto



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ACADEMIC PRESS, INC.  
A Division of Harcourt Brace & Company  
525 B Street, Suite 1900  
San Diego, California 92101-4495

United Kingdom Edition published by  
ACADEMIC PRESS LIMITED  
24-28 Oval Road, London NW1 7DX

Library of Congress Catalog Card Number: 63-16561  
ISBN: 0-12-533018-9

94 95 96 97 98 99 9 8 7 6 5 4 3 2 1

PRINTED IN THE UNITED STATES OF AMERICA

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*Michael A. Lieberman and Richard*

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# Design of High-Density Plasma Sources for Materials Processing

MICHAEL A. LIEBERMAN

*Department of Electrical Engineering and Computer Sciences,  
University of California, Berkeley, California*

and

RICHARD A. GOTTSCHO

*AT&T Bell Laboratories,  
Murray Hill, New Jersey*

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## I. Introduction

The advent of sub-micron electronic device fabrication has brought unprecedented demands for process optimization and control (1,2) which, in turn, have led to improved plasma reactors for the etching and deposition of thin films. As a result, we have witnessed the introduction of a new generation of plasma systems based on electron cyclotron resonance (ECR) heating (3–6). ECR plasma etching of polycrystalline Si, single crystalline Si, silicides, Al, Mo, W, SiO<sub>2</sub>, polymers, and III–V compound semiconductors have all been reported in recent years (7–33). Similarly, ECR plasmas have been used to deposit amorphous Si, silicon nitride, boron carbide, and SiO<sub>2</sub>, to name just a few materials (34–40). Applications of ECR plasmas beyond etching and deposition have also been reported and include ion implantation (41–45), surface cleaning (46–59), surface passivation (60), and oxidation (53,61–63). Besides ECR, many other “novel” plasma generation schemes are now being offered to satisfy manufacturers’ needs in these materials processing areas. All these schemes purport to offer advantages over conventional approaches such as the capacitively coupled radio frequency discharge now used in many factories for etching and deposition of thin films during integrated circuit manufacturing.

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